

Crossed Andreev reflection in a d -wave superconductor with two quantum point contacts

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(December 27, 2003)

We theoretically study the crossed Andreev reflection in a hybrid nanostructure which comprises a d -wave superconductor and two normal-metal quantum wires. When the superconductor of the (110) oriented surface is in contact with the wires parallel and placed close to each other, the Andreev bound state is formed by the crossed Andreev reflection. When the contact barrier potential is sufficiently large, two sharp peaks appear in the conductance well below the gap structure, which originate from the bonding and antibonding Andreev bound states. We propose that these Andreev bound states form a two-level quantum system (qubit).

PACS numbers: 74.45.+c, 74.50.+r, 81.07.Lk, 73.40.Gk

Quantum transport in nanostructures is of current interest in both theoretical and experimental studies. In a quantum wire, its width is so narrow that electron waves are strongly confined in the transverse direction and their transverse momenta are quantized. In a ballistic conduction of electrons through a quantum point contact with width comparable to the Fermi wavelength, a step-like structure with step of $2e^2/h$ appears in the conductance as a function of Fermi energy or width [1–3].

One of the fundamental consequences of superconductivity is the Andreev reflection at the interface of a normal-metal and a superconductor (SC) [4,5]. This phenomenon corresponds to an incoming electron from the normal side being reflected as a hole, thereby adding a Cooper pair in the superconducting condensate. In a tunnel junction of a normal-metal and a (110) oriented d -wave SC, the zero bias conductance peak appears due to the formation of the Andreev bound state at the interface [6,7]. However, when a single quantum wire of a single conducting channel is in contact with d -wave SC of the (110) oriented surface, the Andreev reflection is completely suppressed due to the quantum mechanical diffraction of electron waves at the narrow opening [8].

A basic question arises what happens if two quantum wires are in contact to the (110) oriented d -wave SC (see Fig. 1). When an electron is injected into SC from one of the wires, there is a possibility that the Andreev hole is reflected back into another wire due to the non-local effect called the *crossed* Andreev reflection (CAR) [9,10], thus providing an ideal system to study CAR.

In this Letter, we explore quantum-interference effects due to the crossed Andreev reflection in a d -wave SC with two quantum wires that are parallel and placed close to each other. It is shown that the resonance peak in the conductance is split into two sharp peaks at low energies when the barrier potential of the contact is sufficiently large. The lower and higher energy peaks correspond to the bonding and the antibonding Andreev bound states, respectively. This suggests that these Andreev levels

form a two-level quantum system (qubit), whose population can be controlled by application of bias voltage and/or electromagnetic field, exhibiting a coherent oscillation of the Andreev qubit (Rabi oscillation).

We examine the quantum transport in a hybrid nanostructure of a d -wave SC and two normal-conducting quantum wires. Figure 1 shows a model structure in the x - y plane with a two-dimensional (2D) d -wave SC occupying the left half space, and two quantum wires of width w , lead 1 and lead 2, which are parallel along x and connected to SC at $y = \pm L/2$. The wave functions of electron and hole like quasiparticles with excitation energy E in the electrodes are determined by the Bogoliubov-de Gennes equation

$$\begin{pmatrix} \mathcal{H}_0 & \Delta(\mathbf{k}, \mathbf{r}) \\ \Delta^*(\mathbf{k}, \mathbf{r}) & -\mathcal{H}_0 \end{pmatrix} \begin{pmatrix} u_{\mathbf{k}}(\mathbf{r}) \\ v_{\mathbf{k}}(\mathbf{r}) \end{pmatrix} = E \begin{pmatrix} u_{\mathbf{k}}(\mathbf{r}) \\ v_{\mathbf{k}}(\mathbf{r}) \end{pmatrix}, \quad (1)$$

where $\mathcal{H}_0 = -\hbar^2 \nabla^2 / 2m - \epsilon_F$ is the single-particle Hamiltonian with the Fermi energy $\epsilon_F = \hbar^2 k_F^2 / 2m$. For simplicity, the Fermi wave number k_F and the effective mass m are common for all electrodes, and the amplitude of the gap function $\Delta(\mathbf{k}, \mathbf{r})$ is uniform in SC and vanishes in the wires. In an anisotropic SC, the pair potential $\Delta(\mathbf{k}, \mathbf{r})$ is a function of wave vector $\mathbf{k}$, and its value is defined on the Fermi surface in the direction of $\mathbf{k}$. In leads 1 and 2 with infinite wall boundaries, the wave

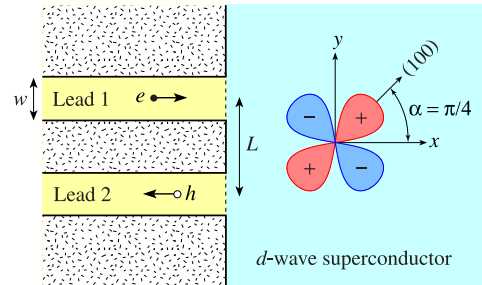


FIG. 1. Schematic diagram of two-leg normal-conducting quantum wires in contact with a d -wave superconductor.

function of an electron propagating along the x axis with wave number k in the n th electron subband is given by the product of the plane wave e^{ikx} and the n th transverse wave, $\chi_n(y - L/2)$ in lead 1 and $\chi_n(y + L/2)$ in lead 2, where $\chi_n(y) = (2/w)^{1/2} \sin[(n\pi/w)(y + w/2)]$, and has the energy $E = (\hbar^2/2m)[k^2 + (n\pi/w)^2] - \epsilon_F$. In the following, we restrict our calculation to the case where only the lowest subband ($n = 1$) is occupied by electrons (or holes) in the wires, which is realized for those wires satisfying $\pi < k_F w < 2\pi$. When an electron with energy E and wave number $k_1 = [2mE + k_F^2 - (\pi/w)^2]^{1/2}$ is incident from lead 1 into SC, the wave functions in leads 1 and 2 are given by $\Psi_1(x, y) = \varphi_1(x)\chi_1(y - L/2)$ and $\Psi_2(x, y) = \varphi_2(x)\chi_1(y + L/2)$, where

$$\varphi_1 = \begin{pmatrix} 1 \\ 0 \end{pmatrix} e^{ik_1 x} + r_{11}^{ee} \begin{pmatrix} 1 \\ 0 \end{pmatrix} e^{-ik_1 x} + r_{11}^{eh} \begin{pmatrix} 0 \\ 1 \end{pmatrix} e^{ik_1 x}, \quad (2)$$

$$\varphi_2 = r_{12}^{ee} \begin{pmatrix} 1 \\ 0 \end{pmatrix} e^{-ik_1 x} + r_{12}^{eh} \begin{pmatrix} 0 \\ 1 \end{pmatrix} e^{ik_1 x}. \quad (3)$$

Here, r_{11}^{ee} and r_{11}^{eh} are the amplitudes of the normal reflection (NR) and Andreev reflection (AR), respectively, while r_{12}^{ee} and r_{12}^{eh} are those of the *crossed* normal reflection (CNR) and the *crossed* Andreev reflection (CAR), respectively. A similar treatment is made for an incident electron from lead 2. Since $E \lesssim \Delta \ll \epsilon_F$, we put $k_1 \approx k_F[1 - (\pi/k_F w)^2]^{1/2}$ in the following.

We employ the Blonder-Tinkham-Klapwijk (BTK) approach [5] to calculate the conductance of the structure. To carry out the calculation analytically, we make the Andreev approximation that neglects all the evanescent modes [11], and put the wave function of SC in the form

$$\Psi_s(x, y) = \int_{-k_F}^{k_F} t_s^{ee}(p_y) \begin{pmatrix} 1 \\ \Gamma_+ \end{pmatrix} e^{i\sqrt{k_F^2 - p_y^2}x} e^{ip_y y} dp_y + \int_{-k_F}^{k_F} t_s^{eh}(p_y) \begin{pmatrix} \Gamma_- \\ 1 \end{pmatrix} e^{-i\sqrt{k_F^2 - p_y^2}x} e^{ip_y y} dp_y, \quad (4)$$

where $\Gamma_+ = \Delta_+^*/(E + \Omega_+)$ and $\Gamma_- = \Delta_-/(E + \Omega_-)$ with $\Omega_{\pm} = \sqrt{E^2 - |\Delta_{\pm}|^2}$ [6–8]. The first and second terms in Eq. (4) are the transmitted QP waves on the electron-like and hole-like branches, respectively. In SC of d -wave symmetry, QPs in different branches feel different pair potentials, $\Delta_+ = \Delta_0 \cos 2(\theta - \alpha)$ and $\Delta_- = \Delta_0 \cos 2(\theta + \alpha)$, where α is the angle between the (100) axis of SC and the normal to the interface (see Fig. 1), and $\theta = \sin^{-1}(p_y/k_F)$ is the propagation angle relative to the x axis.

In the following, we focus on the (110) oriented surface of SC, i.e., $\alpha = \pi/4$, as shown in Fig. 1. In this case, QPs in the electron-like and hole-like branches move in the pair potentials of opposite sign, $\Delta_{\pm} = \pm\Delta$, where $\Delta = 2\Delta_0(p_y/k_F)\sqrt{1 - (p_y/k_F)^2}$, and $\Omega_{\pm} = \Omega = \sqrt{E^2 - \Delta^2}$. The barrier potential at the interface between the wires and SC is taken into account by the δ -function-type potential with amplitude $(\hbar^2 k_F/2m)Z$, Z being a dimensionless parameter [5]. The boundary conditions for the

wave functions at the interfaces are $\Psi_s(0, y) = \Psi_i(0, y)$ and $[\partial_x \Psi_s(x, y) - \partial_x \Psi_i(x, y)]_{x=0} = k_F Z \Psi_i(0, y)$ ($i = 1, 2$) appropriate for the $\delta(x)$ potential. The matching technique to the boundary conditions [3] yields the reflection coefficients

$$r_{11}^{ee} = -1 + \frac{\bar{k}_1}{\mathcal{D}_+}(\bar{k}_1 + \mathcal{F} - \mathcal{G}_c - iZ) + \frac{\bar{k}_1}{\mathcal{D}_-}(\bar{k}_1 + \mathcal{F} + \mathcal{G}_c - iZ), \quad (5)$$

$$r_{11}^{eh} = -\bar{k}_1 \mathcal{G}_s \left(\frac{1}{\mathcal{D}_-} - \frac{1}{\mathcal{D}_+} \right), \quad (6)$$

$$r_{12}^{ee} = -\frac{2\bar{k}_1 \mathcal{G}_c}{\mathcal{D}_+ \mathcal{D}_-} [(\bar{k}_1 + \mathcal{F} - iZ)^2 - (\mathcal{G}_c^2 + \mathcal{G}_s^2)], \quad (7)$$

$$r_{12}^{eh} = -\bar{k}_1 \mathcal{G}_s \left(\frac{1}{\mathcal{D}_-} + \frac{1}{\mathcal{D}_+} \right), \quad (8)$$

with $\bar{k}_1 = k_1/k_F$, $\mathcal{D}_{\pm} = (\bar{k}_1 + \mathcal{F})^2 - (\mathcal{G}_c \pm iZ)^2 - \mathcal{G}_s^2$, and

$$\mathcal{F} = \int_{-k_F}^{k_F} \frac{dp}{2\pi} \frac{\Omega}{E} \sqrt{1 - (p/k_F)^2} \varphi^2(p), \quad (9)$$

$$\mathcal{G}_c = \int_{-k_F}^{k_F} \frac{dp}{2\pi} \frac{\Omega}{E} \sqrt{1 - (p/k_F)^2} \varphi^2(p) \cos(pL), \quad (10)$$

$$\mathcal{G}_s = i \int_{-k_F}^{k_F} \frac{dp}{2\pi} \frac{\Delta}{E} \sqrt{1 - (p/k_F)^2} \varphi^2(p) \sin(pL), \quad (11)$$

where $\varphi(p) = \langle p | \chi_1 \rangle$ is the overlap integral of $\chi_1(y)$ and e^{ipy} :

$$\varphi(p) = \sqrt{8w/\pi^2} \cos(pw/2) / [1 - (pw/\pi)^2]. \quad (12)$$

Note that $\mathcal{F}$ in Eq. (9) represents the local coupling and is independent of distance L , while $\mathcal{G}_c$ and $\mathcal{G}_s$ represent the non-local coupling and are dependent on L . In the limit of $L \rightarrow \infty$, where the two contacts are independent ($\mathcal{G}_c = \mathcal{G}_s = 0$), one has $r_{11}^{ee} = (k_1 - \mathcal{F} - iZ)/(k_1 + \mathcal{F} + iZ)$, $r_{11}^{eh} = r_{12}^{ee} = r_{12}^{eh} = 0$, recovering the complete suppression of AR in a single quantum wire with a single transverse mode [8]. The reflection coefficients r_{22}^{ee} , r_{22}^{eh} , r_{21}^{ee} , and r_{21}^{eh} for an incident electron from lead 2 are obtained from those in Eqs. (5)-(8) by the replacement $1 \leftrightarrow 2$ and $L \rightarrow -L$. It follows from Eqs. (6)-(8) that, when there is no barrier potential ($Z = 0$) at the interface, AR is absent ($r_{11}^{eh} = 0$), whereas CNR and CAR are finite with the ratio $r_{12}^{ee}/r_{12}^{eh} = \mathcal{G}_c/\mathcal{G}_s$.

When bias voltage V is applied to the two leads, the conductance G at zero temperature ($T = 0$) is given by

$$G = \frac{4e^2}{h} (1 - |r_{11}^{ee}|^2 - |r_{12}^{ee}|^2 + |r_{11}^{eh}|^2 + |r_{12}^{eh}|^2)_{E=eV}, \quad (13)$$

where h is the Planck constant. Figure 2 shows the conductance G vs V for $k_F w = 4$, $k_F L = 8$, and different values of Z . The conductance is normalized by the normal state value $G_N = G(\Delta = 0)$, which takes $G_N \sim 16(e^2/h)(k_1/k_F)\mathcal{F}_N/Z^2$ ($Z \gg 1$) with $\mathcal{F}_N = \mathcal{F}(\Delta = 0)$.

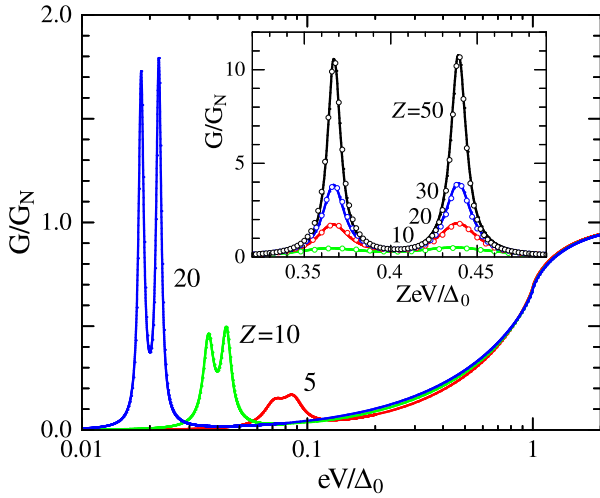


FIG. 2. Normalized conductance G/G_N as a function of bias voltage V for different values of interfacial barrier parameter Z . Inset shows G/G_N vs normalized voltage ZV . The circles in the inset are calculated from Eq. (16).

For a low barrier potential of small Z , the conductance decreases monotonically with decreasing eV below Δ_0 . As the barrier potential becomes higher, a peak structure appears well below Δ_0 and shifts towards lower eV , developing the double peak structure with increasing Z . If the conductance is plotted as a function of normalized voltage ZV as shown in the inset, the conductance peaks fall into the same position, indicating that the resonance peak positions are scaled by $1/Z$.

Let us examine the origin of the double peak structure in the conductance for the tunneling case ($Z \gg 1$). Since $\Omega \approx i|\Delta|$ for $E \ll \Delta_0$, $\mathcal{F}$, $\mathcal{G}_c$, and $\mathcal{G}_s$ in Eqs. (9)-(11) have the forms: $\mathcal{F} \approx if\Delta_0/E$, $\mathcal{G}_c \approx ig_c\Delta_0/E$, and $\mathcal{G}_s \approx ig_s\Delta_0/E$, where $f = (E\mathcal{F}/i\Delta_0)_{E \rightarrow 0}$, $g_c = (E\mathcal{G}_c/i\Delta_0)_{E \rightarrow 0}$, and $g_s = (E\mathcal{G}_s/i\Delta_0)$ are energy independent quantities, so that the Andreev reflection coefficients are calculated in the resonance forms

$$r_{11}^{eh} \approx -\frac{ig\gamma}{E - E_- + i\gamma} + \frac{ig\gamma}{E - E_+ + i\gamma}, \quad (14)$$

$$r_{12}^{eh} \approx -\frac{ig\gamma}{E - E_- + i\gamma} - \frac{ig\gamma}{E - E_+ + i\gamma}, \quad (15)$$

where $g = g_s/2f$, $E_{\pm} = (f \pm |g_c| + g_s^2/2f)\Delta_0/Z$, and $\gamma = (k_1/k_F)f\Delta_0/Z^2$. The other coefficients are $r_{11}^{ee} \approx -1 - gr_{12}^{eh}$ and $r_{12}^{ee} \sim O(g^2)$. The resonance energies $E_{\pm}$ and intensity g depend strongly on lead separation L , exhibiting damped oscillations with the period of the Fermi wave length $\lambda_F = 2\pi/k_F$. We note that the resonance positions $E_{\pm}$ and their separation $E_+ - E_-$ are scaled by $1/Z$, while the line width γ is scaled by $1/Z^2$. For $Z \gg 1$, the line width of the peaks is much smaller than the separation, and therefore a well-separated two-peak structure is formed as shown in the inset of Fig. 2. In this case, the conductance G is written as the sum of two Lorentzians

$$\frac{G}{G_N} \approx \frac{\mathcal{I}\gamma/\pi}{(eV - E_+)^2 + \gamma^2} + \frac{\mathcal{I}\gamma/\pi}{(eV - E_-)^2 + \gamma^2}, \quad (16)$$

where $\mathcal{I} = (\pi g^2 f/4\mathcal{F}_N)$. The simple formula (16) reproduces the numerical result in the inset of Fig. 2, if the calculated values ($f = 0.405$, $g_c = -0.036$, $g_s = -0.0345$, and $\mathcal{F}_N = 0.68$) are used in Eq. (16). Note that the peak height of G/G_N increases in proportion to Z^2 .

To elucidate the formation of the Andreev bound states, we calculate the QP wave function $\Psi_s(x, y) = {}^t(\Psi_s^e, \Psi_s^h)$ in SC, where Ψ_s^e and Ψ_s^h are the electron and hole wave functions, respectively. Figure 3 shows the mapping of the absolute squares, $|\Psi_s^e|^2$ and $|\Psi_s^h|^2$, at the resonance energies on the xy plane for $k_F w = 5$, $k_F L = 8$, and $Z = 50$, when an electron is incident from lead 1. It is clearly seen that the QP wave functions are strongly localized with very large peaks (red color) near the contacts due to the formation of the Andreev bound states, and that the decaying QP waves are traced to the (010) and (0 $\bar{1}$ 0) directions along which multiple reflections of electron and hole take place. It is also seen that the formation of the localized states, especially the relative position of the peaks with respect to the contacts, is different between the electron and hole QPs, and between the resonance energies $E_{\pm}$. For $Z \gg 1$ and around $E_{\pm}$, the explicit form of Ψ_s inside SC is obtained as

$$\Psi_s \approx \frac{i\gamma}{E - E_- + i\gamma} \begin{pmatrix} \psi_-^e \\ \psi_-^h \end{pmatrix} + \frac{i\gamma}{E - E_+ + i\gamma} \begin{pmatrix} \psi_+^e \\ \psi_+^h \end{pmatrix},$$

where, except very close to the interface ($x \approx 0$),

$$\begin{pmatrix} \psi_-^e \\ \psi_-^h \end{pmatrix} = \frac{2g}{\pi} \int_0^{k_F} \frac{\Delta}{E} \varphi(p) \cos \frac{pL}{2} \sin qx \begin{pmatrix} \sin py \\ -\cos py \end{pmatrix} dp, \\ \begin{pmatrix} \psi_+^e \\ \psi_+^h \end{pmatrix} = \frac{2g}{\pi} \int_0^{k_F} \frac{\Delta}{E} \varphi(p) \sin \frac{pL}{2} \sin qx \begin{pmatrix} \cos py \\ \sin py \end{pmatrix} dp,$$

with $q = \sqrt{k_F^2 - p^2}$ and $\Delta = 2\Delta_0 pq/k_F^2$. At lower resonance energy E_- , Ψ_s is dominated by the first term whose electron (hole) wave function ψ_-^e (ψ_-^h) is an odd (even) function of y . At higher resonance energy E_+ , Ψ_s is dominated by the second term whose electron (hole) wave function ψ_+^e (ψ_+^h) is an even (odd) function of y . These results indicate that the electron (hole) wave functions at the lower and higher bound states have different parity with respect to y . It is noteworthy that the Andreev holes are reflected back into leads 1 and 2 in phase at E_- and out of phase at E_+ (cf. Eqs. (14) and (15)).

The Andreev bound states appeared in the present system have the following implication. When the interface barrier potential is very high ($Z \gg 1$), the current flows through the system via the Andreev bound states with very sharp energy levels at $E_{\pm}$. When the bias voltage V is set between $V_- = E_-/e$ and $V_+ = E_+/e$ of the conductance peaks, the lower bound state at E_- is occupied by Andreev quasiparticles while the higher-energy bound state at E_+ is empty; the lower bound state is viewed as

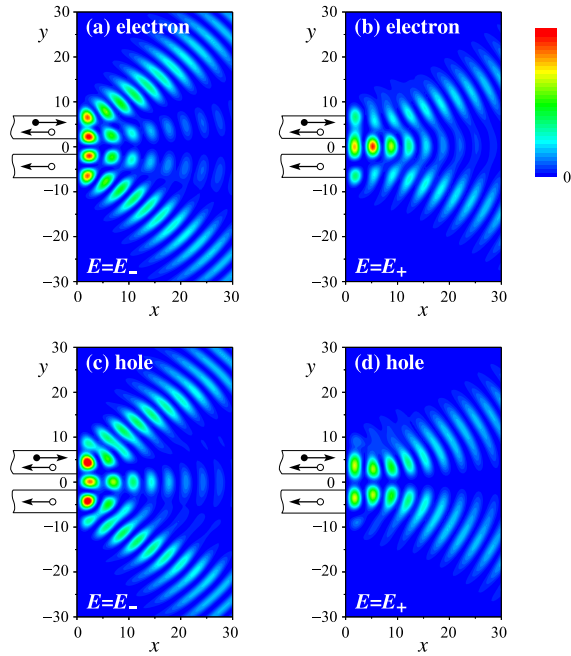


FIG. 3. Mapping of Andreev bound states on the xy plane, when an electron is incident from lead 1 to a d -wave SC. (a) and (b) are the absolute square of electron wave functions $|\Psi_s^e|^2$ at energies E_- and E_+ ; (c) and (d) are that of hole wave functions $|\Psi_s^h|^2$ at E_- and E_+ .

the ground state and the upper bound state as the excited state, and therefore the system in this setup forms a two-level quantum system (qubit). For simplicity, we denote the ground state and excited state by $|0\rangle$ and $|1\rangle$, respectively. The Andreev bound states of electron (hole) QP at E_- and E_+ have dipole moments $\langle 1|y|0\rangle$ due to the different parity of the states with respect to y . Therefore application of the electric field $eE_0 \cos(\omega t)$ oscillating along y causes a significant Rabi oscillation with frequency $\mathcal{V} = eE_0 \langle 1|y|0\rangle / \hbar$ between the Andreev bound states, if ω is tuned to the resonance condition $\omega = E_+ - E_-$ and the damping rate γ of the states is substantially smaller than $\hbar\mathcal{V}$. The significant coherence oscillation requires a smaller damping γ , which is achieved by inserting tunnel barriers at the interfaces. The controlled evolution between the two states $|0\rangle$ and $|1\rangle$ is realized by applying resonant microwaves to the system. The two level Andreev bound states in the proposed system provides a new possibility of superconducting qubit (d -wave Andreev level qubit) [12].

The realization of quantum two-level systems (qubit) is fundamental issues in both physics and information technologies, because qubits are basic elements for quantum computation [13]. Recently, the coherent manipulation of the states in two-level systems has been demonstrated in nanostructured superconducting circuits [14,15].

In summary, we have theoretically studied the quantum-interference effects caused by the crossed Andreev reflection in a hybrid nanostructure which com-

prises a d -wave superconductor and normal-conducting quantum wires. When a superconductor of the (110) oriented surface is in contact with the two-leg quantum wires via tunnel barriers, the resonance bound states are formed at low energies due to the crossed Andreev reflection. As a consequence, two well-separated sharp peaks appear in the conductance well below the superconducting gap structure. The lower and higher conductance peaks correspond to the bonding and the antibonding Andreev bound states whose wave functions have different parity. We propose that these Andreev bound states form a two-level quantum system (d -wave Andreev level qubit), which can be controlled by application of bias voltage and/or radiation of oscillating electric field.

This work was supported by a Grant-in-Aid for from MEXT, NAREGI, and CREST, Japan.

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- [1] B. J. van Wees *et al.*, Phys. Rev. Lett. **60**, 848 (1988)
 - [2] D. A. Wharam *et al.*, J. Phys. C **21** L209 (1988).
 - [3] A. Szafer and A. D. Stone, Phys. Rev. Lett. **62**, 300 (1989); L. I. Glazman *et al.*, Pis'ma Zh. Eksp. Teor. Fiz. **48**, 218 (1988) [JETP Lett. **48**, 238 (1988)]; G. Kirichenow, Phys. Rev. B **39**, 10 452 (1989).
 - [4] A. F. Andreev, Zh. Eksp. Teor. Fiz. **46**, 1823 (1964) [Sov. Phys. JETP **19**, 1228 (1964)].
 - [5] G. E. Blonder, M. Tinkham, and T. M. Klapwijk, Phys. Rev. B. **25**, 4515 (1982).
 - [6] C. R. Hu, Phys. Rev. Lett. **72**, 1526 (1994); Y. Tanaka and S. Kashiwaya, *ibid.* **74**, 3451 (1995); M. Matsumoto and H. Shiba, J. Phys. Soc. Jpn. **64**, 1703 (1995).
 - [7] S. Kashiwaya *et al.*, Phys. Rev. B **51** 1350 (1995); S. Kashiwaya and Y. Tanaka, Rep. Prog. Phys. **63**, 1641 (2000).
 - [8] Y. Takagaki and K. H. Ploog, Phys. Rev. B **60**, 9750 (1999); K. Tsuchikawa *et al.*, Physica C **362**, 224 (2001).
 - [9] J. M. Bayers and M. E. Flatté, Phys. Rev. Lett. **74**, 306 (1995).
 - [10] G. Deutscher and D. Feinberg, Appl. Phys. Lett. **76**, 487 (2000); G. Falci *et al.*, Europhys. Lett. **54**, 255 (2001); R. Melin, J. Phys. C **13**, 6445 (2001); T. Yamashita *et al.*, Phys. Rev. B **68**, 174504 (2003).
 - [11] This is a good approximation when the width of the leads satisfies the condition $1.5 \lesssim k_F w / \pi < 2$ [8].
 - [12] An s -wave Andreev level qubit in a SQUID with a quantum point contact has been studied by A. Zazunov *et al.*, Phys. Rev. Lett. **90**, 87003 (2003).
 - [13] M. A. Nielsen and I. L. Chuang, *Quantum Computation and Quantum Information* (Cambridge University Press, Cambridge, 2000).
 - [14] Y. Nakamura *et al.*, Nature (London) **398**, 786 (1999); T. Yamamoto *et al.*, *ibid.*, **425**, 941 (2003).
 - [15] D. Vion *et al.*, Science **296**, 886 (2002); Y. Yu *et al.*, Science **296**, 889 (2002); I. Chiorescu *et al.*, Science **299**, 1869 (2003); J. M. Martinis *et al.*, Phys. Rev. Lett. **89**, 117901 (2002); Y. Makhlin *et al.*, Rev. Mod. Phys. **73**, 357 (2001).